

FDC6432SH

12V P-Channel PowerTrench® MOSFET, 30V PowerTrench® SyncFET

General Description

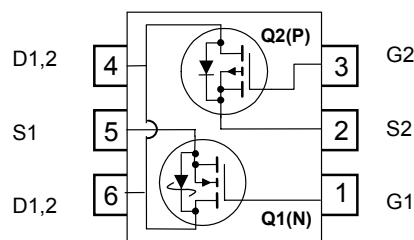
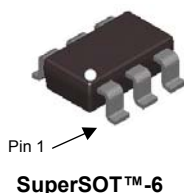
This complementary P-Channel MOSFET with SyncFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for providing an extremely low $R_{DS(ON)}$ in a small package.

Applications

DC/DC converter
Power management

Features

- SyncFET $R_{DS(ON)} = 90\text{ m}\Omega @ V_{GS} = 10\text{ V}$
2.4 A, 30V $R_{DS(ON)} = 105\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
- P channel $R_{DS(ON)} = 90\text{ m}\Omega @ V_{GS} = -4.5\text{ V}$
-2.5 A, -12V $R_{DS(ON)} = 125\text{ m}\Omega @ V_{GS} = -2.5\text{ V}$
 $R_{DS(ON)} = 220\text{ m}\Omega @ V_{GS} = -1.8\text{ V}$
- Fast switching speed.
- High performance trench technology for extremely low $R_{DS(ON)}$



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings		Units
		Q1 (N)	Q2 (P)	
V_{DSS}	Drain-Source Voltage	30	-12	V
V_{GSS}	Gate-Source Voltage	± 16	± 8	V
I_D	Drain Current— Continuous (Note 1a) — Pulsed	2.4	-2.5	A
		7	-7	
P_D	Power Dissipation for Single Operation (Note 1a) (Note 1b)	1.3		W
		0.7		
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150		$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a) (Note 1b)	100	$^\circ\text{C/W}$
		175	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	60	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.432	FDC6432SH	7"	8mm	3000 units

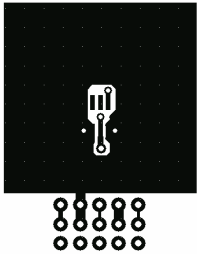
Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted							
Symbol	Parameter	Test Conditions	Q	Min	Typ	Max	Units
Off Characteristics							
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$ $V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	Q1 Q2	30 -12			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 1\text{ mA}$, Ref to 25°C $I_D = -250\text{ }\mu\text{A}$, Ref to 25°C	Q1 Q2		25 -10		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$ $V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}$	Q1 Q2			500 1	μA
I_{GSS}	Gate-Body Leakage	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$ $V_{GS} = \pm 8\text{ V}, V_{DS} = 0\text{ V}$	Q1 Q2			± 100 ± 100	nA
On Characteristics							
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$ $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	Q1 Q2	1 -0.4	1.5 -0.7	3 -1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 1\text{ mA}$, Ref to 25°C $I_D = -250\text{ }\mu\text{A}$, Ref to 25°C	Q1 Q2		-7 3		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 2.4\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 2.2\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 2.4\text{ A}, T_J = 125^\circ\text{C}$	Q1		75 85 100	90 105 140	$\text{m}\Omega$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -4.5\text{ V}, I_D = -2.5\text{ A}$ $V_{GS} = -2.5\text{ V}, I_D = -2.0\text{ A}$ $V_{GS} = -1.8\text{ V}, I_D = -1.6\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = 2.5\text{ A}, T_J = 125^\circ\text{C}$	Q2		75 97 154 86	90 125 220 120	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$ $V_{DS} = -5\text{ V}, I_D = -2.5\text{ A}$	Q1 Q2		7 7		S
R_G	Gate Resistance	$V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$	Q1 Q2		5 13		Ω
Dynamic Characteristics							
C_{iss}	Input Capacitance	For Q1: $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ For Q2: $V_{DS} = -6\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	Q1 Q2		270 514		pF
C_{oss}	Output Capacitance		Q1 Q2		50 234		pF
C_{rss}	Reverse Transfer Capacitance		Q1 Q2		20 167		pF
Switching Characteristics (Note 2)							
$t_{d(on)}$	Turn-on Delay Time	For Q1: $V_{DS} = 15\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$ For Q2: $V_{DS} = -10\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\text{ }\Omega$	Q1 Q2		5 13	10 23	ns
t_r	Turn-on Rise Time		Q1 Q2		8 12	16 22	ns
$t_{d(off)}$	Turn-off Delay Time		Q1 Q2		18 22	32 35	ns
t_f	Turn-off Fall Time		Q1 Q2		1.2 2.9	2.4 46	ns
Q_g	Total Gate Charge		Q1 Q2		2.5 5.7	3.5 8	nC
Q_{gs}	Gate-Source Charge		Q1 Q2		0.7 1.2		nC
Q_{gd}	Gate-Drain Charge	Q1 Q2		0.6 1.7		nC	

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

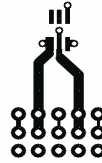
Symbol	Parameter	Test Conditions	Q	Min	Typ	Max	Units
Drain-Source Diode Characteristics							
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 0.7\text{ A}$, Note 2	Q1		0.6	700	mV
		$V_{GS} = 0\text{ V}, I_S = -0.8\text{ A}$, Note 2	Q2		-0.7	1200	
t_{RR}	Reverse Recovery Time	For Q1: $I_F = 2.4\text{ A}, dI_F/dt = 300\text{ A}/\mu\text{s}$	Q1		10		ns
			Q2		24		
I_{RM}	Maximum Reverse Recovery Current	For Q2: $I_F = -2.5\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}$	Q1		0.8		A
			Q2		-0.5		
Q_{RR}	Reverse Recovery Charge		Q1		4		nC
			Q2		6		

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 100°C/W when mounted on a 1 in^2 pad of 2 oz copper



b) 175°C/W when mounted on a minimum pad of 2 oz copper

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < $300\mu\text{s}$, Duty Cycle < 2.0%

Typical Characteristics : Q1

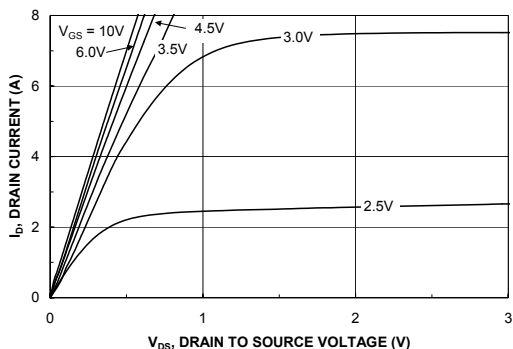


Figure 1. On-Region Characteristics.

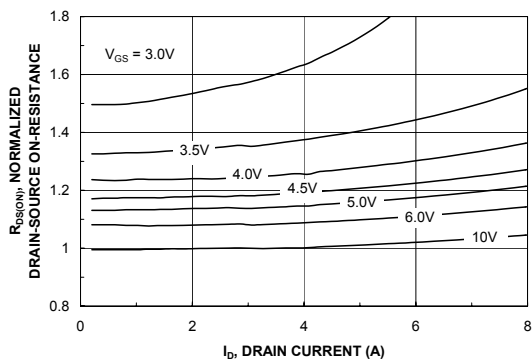


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

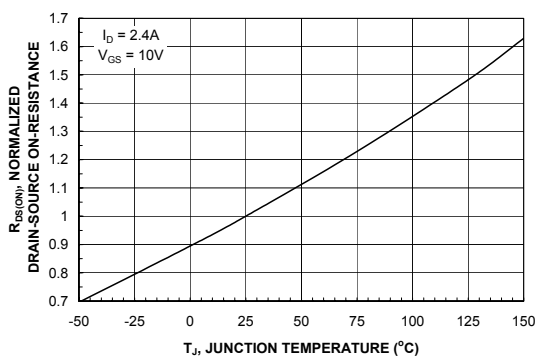


Figure 3. On-Resistance Variation with Temperature.

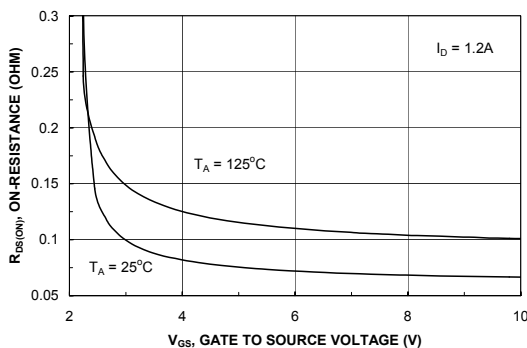


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

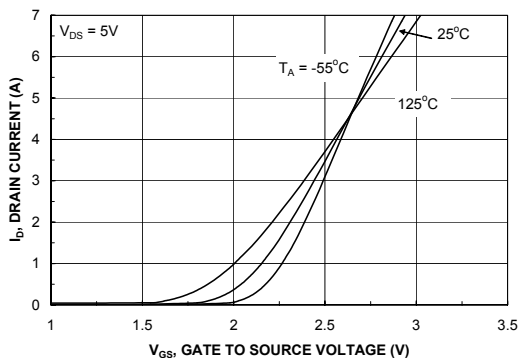


Figure 5. Transfer Characteristics.

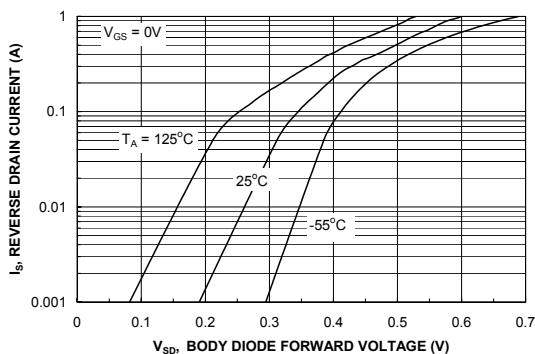


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics : Q1

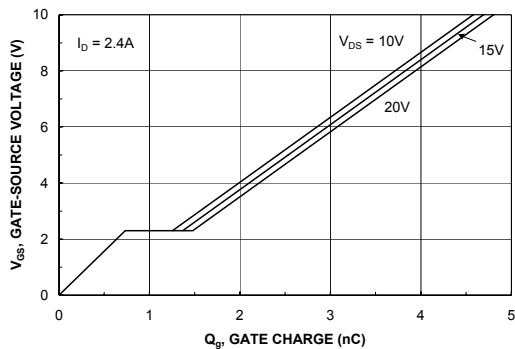


Figure 7. Gate Charge Characteristics.

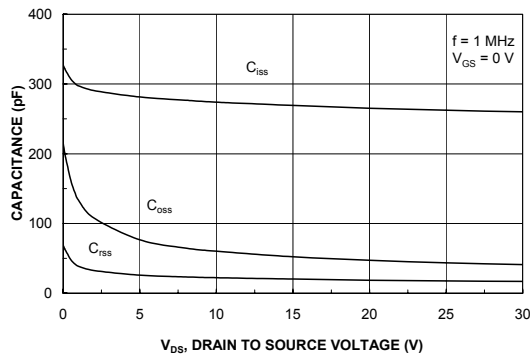


Figure 8. Capacitance Characteristics.

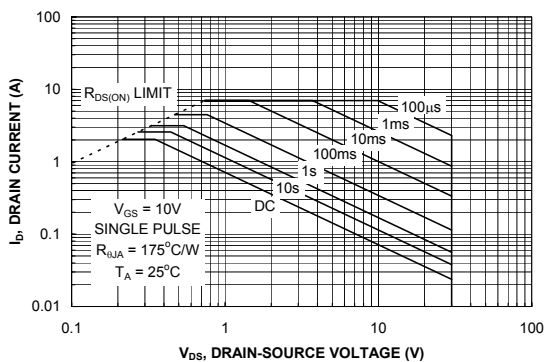


Figure 9. Maximum Safe Operating Area.

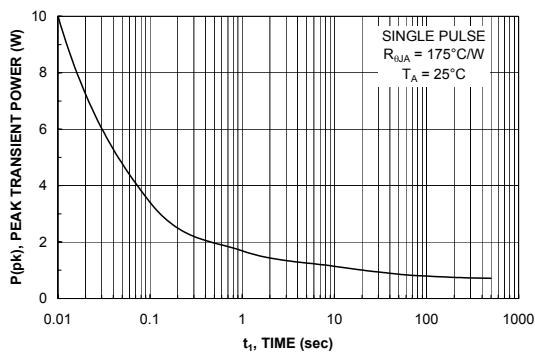


Figure 10. Single Pulse Maximum Power Dissipation.

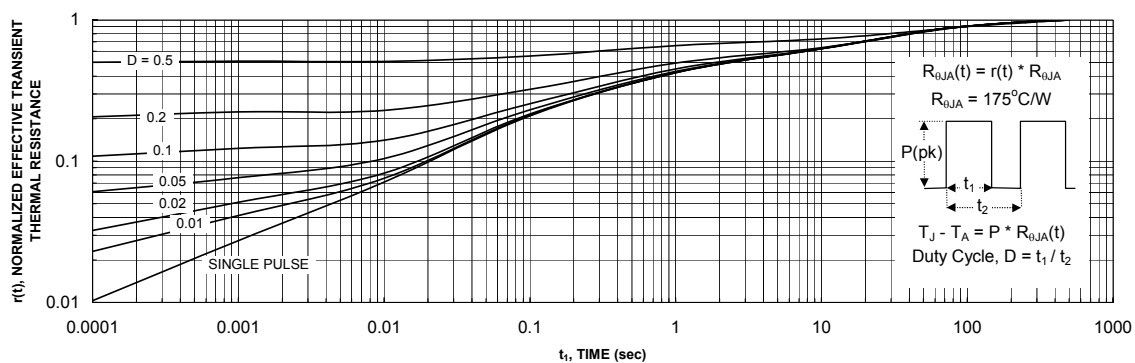


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

Typical Characteristics : Q2

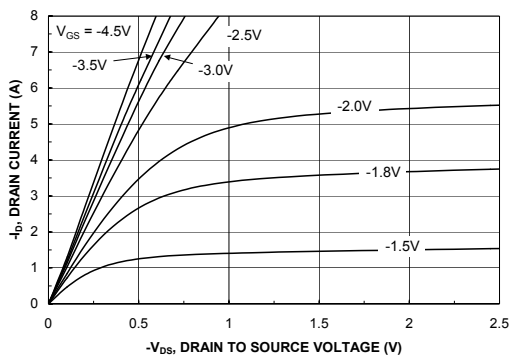


Figure 12. On-Region Characteristics.

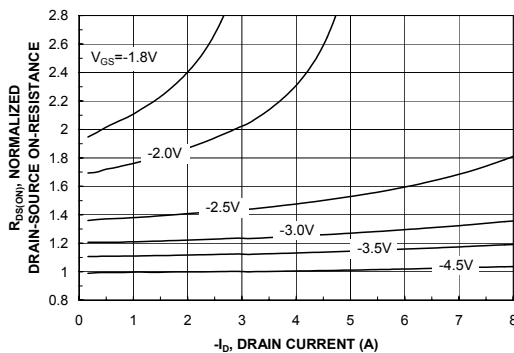


Figure 13. On-Resistance Variation with Drain Current and Gate Voltage.

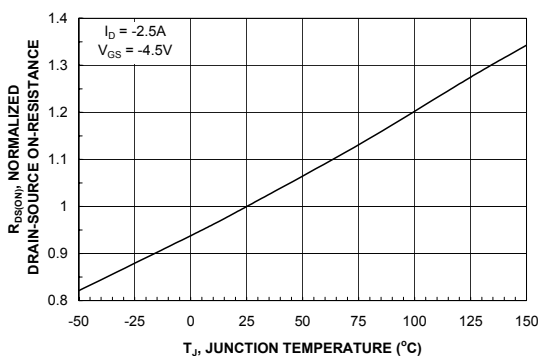


Figure 14. On-Resistance Variation with Temperature.

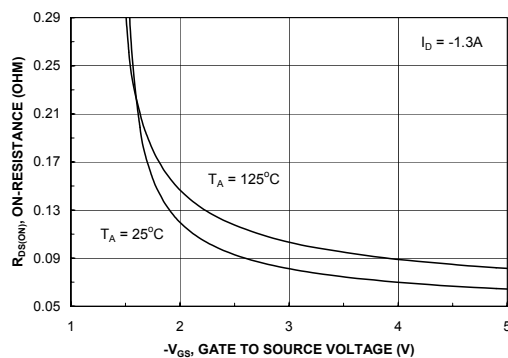


Figure 15. On-Resistance Variation with Gate-to-Source Voltage.

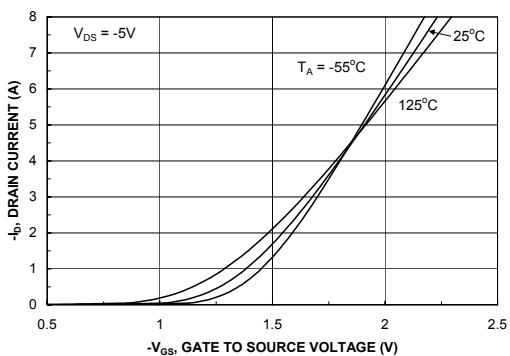


Figure 16. Transfer Characteristics.

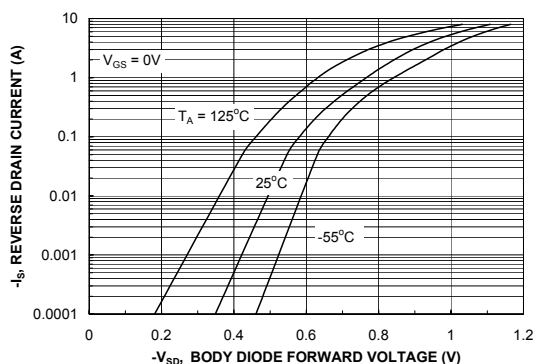


Figure 17. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics : Q2

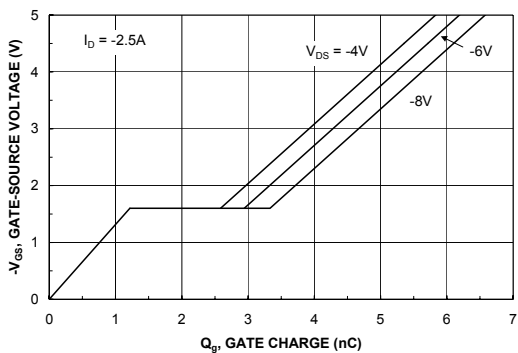


Figure 18. Gate Charge Characteristics.

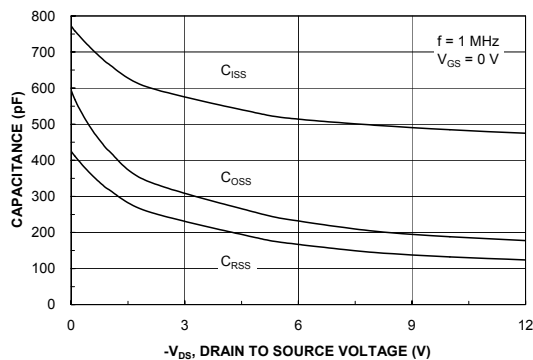


Figure 19. Capacitance Characteristics.

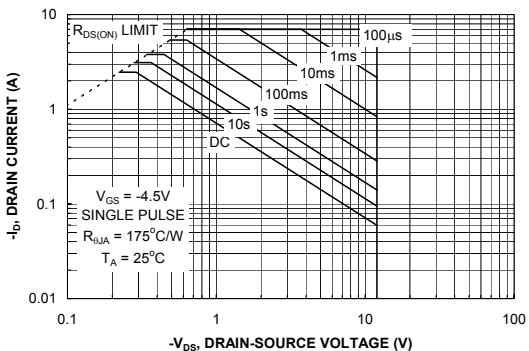


Figure 20. Maximum Safe Operating Area.

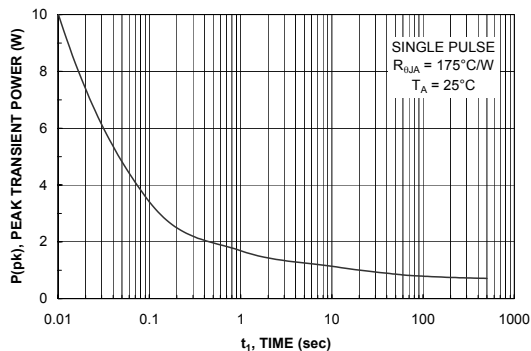


Figure 21. Single Pulse Maximum Power Dissipation.

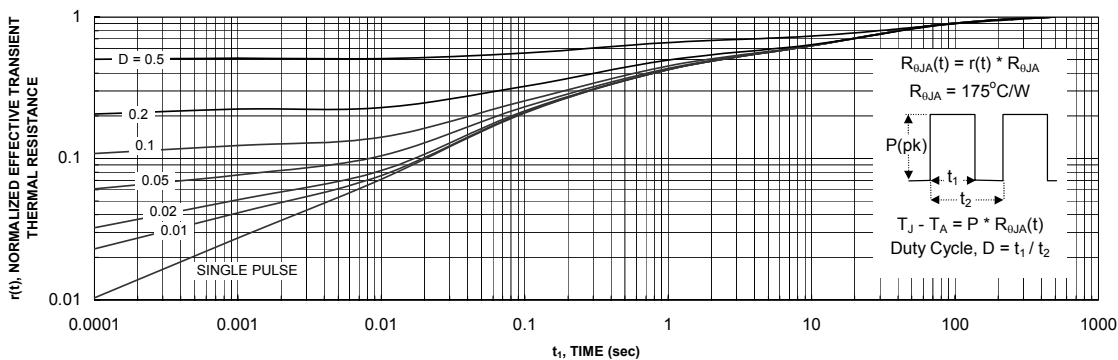


Figure 22. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FACT™	ImpliedDisconnect™	PACMAN™	SPM™
ActiveArray™	FACT Quiet Series™	ISOPLANAR™	POP™	Stealth™
Bottomless™	FAST®	LittleFET™	Power247™	SuperSOT™-3
CoolFET™	FASTr™	MicroFET™	PowerTrench®	SuperSOT™-6
CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
DOME™	GlobalOptoisolator™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic®
E ² CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	µC™	OCX™	RapidConfigure™	UHC™
Across the board. Around the world.™		OCXPro™	RapidConnect™	UltraFET®
The Power Franchise™		OPTOLOGIC®	SILENT SWITCHER®	VCX™
Programmable Active Droop™		OPTOPLANAR™	SMART START™	

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.